

## IL350/351/358/359 HIGH PERFORMANCE LINEAR OPTOCOUPLER for Optical DAA in Telecommunications

Preliminary Data Sheet

### FEATURES

- 2 mm High SMT Package
- High Sensitivity (K1) at Low Operating LED Current
- Couples AC and DC Signals
- Low Input-Output Capacitance
- Isolation Voltage, 2500 V<sub>RMS</sub>
- Low Distortion

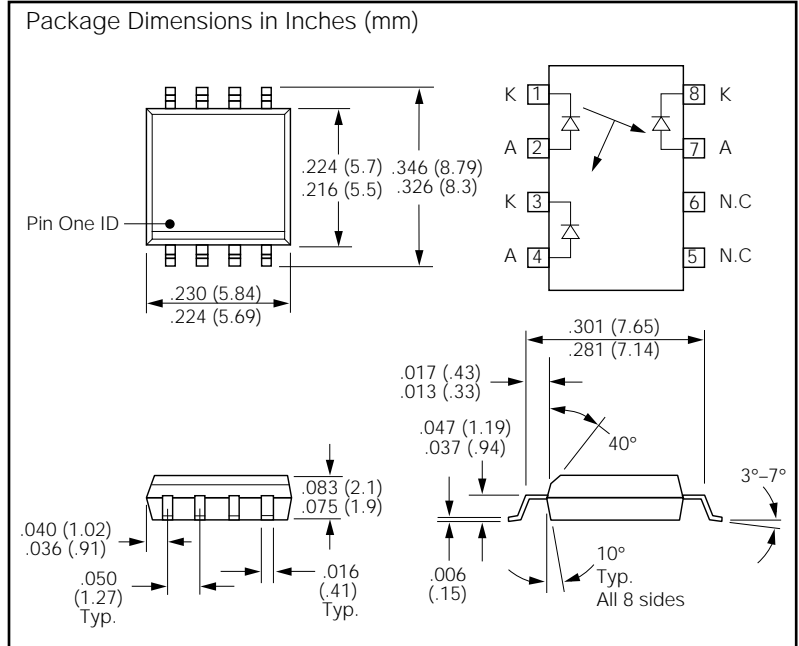
### APPLICATIONS

- Optical DAA for V.34 FAX/Modem PCMCIA Cards
- Digital Telephone Line Isolation

### DESCRIPTION

The IL350/1/8/9 family of Linear Optocoupler consist of an IRLED optically coupled to two photodiodes. The emitter mechanically faces both diodes enabling them to receive approximately an equal amount of infrared light. The diodes produce a proportional amount of photocurrents. The ratio of the photocurrents stays constant with high accuracy when either the LED current changes or the ambient temperature changes. Thus one can control the output diode current optically by controlling the input photodiode current.

The IL350/1/8/9 optocouplers can be used with the aid of operational amplifiers in closed loop conditions to achieve highly linear and electrically isolated AC and or DC signal amplifiers.



### Absolute Maximum Ratings

Emitter	Sym	Min.	Max.	Units
Reverse Voltage	V <sub>R</sub>		3	V
Forward Current	I <sub>F</sub>		30	mA
Surge Current Pulse Width < 10 μs	I <sub>PK</sub>		150	mA
Power Dissipation, T <sub>A</sub> =25°C	P <sub>LED</sub>		150	mW
Derate Linearly from 25°C			2	mW/°C
Junction Temperature	T <sub>J</sub>		100	°C
<b>Detector (each)</b>				
Reverse Voltage	V <sub>R</sub>		15	V
Power Dissipation	P		50	mW
Derate Linearly from 25°C			0.65	mW/°C
Junction Temperature	T <sub>J</sub>		100	°C
<b>Coupler</b>				
Isolation Test Voltage	V <sub>ISOL</sub>	2500		V <sub>RMS</sub>
Total Package Power Dissipation	P <sub>t</sub>		250	mW
Derate Linearly from 25°C			2.8	mW/°C
Storage Temperature	T <sub>S</sub>	-40	150	°C
Operating Temperature	T <sub>OP</sub>	0	75	°C
Lead Soldering Time at 260°C			10	sec.
Isolation Resistance V <sub>IO</sub> =500 V, T <sub>A</sub> =25°C V <sub>IO</sub> =500 V, T <sub>A</sub> =100°C			10 <sup>12</sup> Ω 10 <sup>11</sup> Ω	

**Electrical Characteristics (T<sub>A</sub>=25°C)**

<b>LED Emitter</b>		<b>Symbol</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Units</b>	<b>Test Conditions</b>
Forward Voltage		V <sub>F</sub>		1.8	2.1	V	I <sub>F</sub> =10 mA
Reverse Current		I <sub>R</sub>		.01	10	μA	V <sub>R</sub> =3 V
V <sub>F</sub> Temperature Coefficient		ΔV <sub>F</sub> /Δ°C		-2.2		mV/°C	
Junction Capacitance		C <sub>J</sub>		TBD		pF	V <sub>F</sub> =0 V, f=1 MHz
Dynamic Resistance		ΔV <sub>F</sub> /ΔI <sub>F</sub>		6		W	I <sub>F</sub> =2.5 mA ΔI <sub>F</sub> =1 mA
Switching Time IL358/9		t <sub>F</sub>		40		ns	
		t <sub>R</sub>		40		ns	
<b>Detector</b>							
Junction Capacitance		C <sub>J</sub>		12		pF	V <sub>F</sub> =0 V, f=1 MHz
NEP				<4 <sup>-14</sup>		W/√Hz	V <sub>DET</sub> =0 V
<b>AC Characteristics Photovoltaic Mode</b>							
Frequency Response	IL358/9	BW(-3dB)		1.0		MHz	I <sub>P1</sub> =25 μA Modulation current ΔI <sub>P1</sub> =±6 μA
Phase Response				45		Deg.	
Rise Time				350		ns	
<b>Package</b>							
Input-Output Capacitance		C <sub>IO</sub>		1		pF	V <sub>F</sub> =0 V, f=1 MHz
Common Mode Capacitance		C <sub>cm</sub>		0.5		pF	V <sub>F</sub> =0 V, f=1 MHz
<b>Coupled Characteristics</b>							
				<b>K1 at I<sub>F</sub>=2 mA, V<sub>D</sub>=0 V</b>			<b>K3 Bins</b>
				<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	
IL350				0.003			A-J
IL351				0.005			D, E, F, G
IL358				0.008			D, E, F, G
IL359				0.008			E, F

**Bin Table**

<b>Bin</b>	<b>Min.</b>	<b>Max.</b>
A	0.557	0.626
B	0.620	0.696
C	0.690	0.773
D	0.765	0.859
E	0.851	0.955
F	0.945	1.061
G	1.051	1.181
H	1.169	1.311
I	1.297	1.456
J	1.442	1.618